

PATENT ASSIGNMENT

Electronic Version v1.1
 Stylesheet Version v1.1

| SUBMISSION TYPE: | NEW ASSIGNMENT | | | | | | | | | | |
|--|--------------------------------|---------------|-------------------------------|---------------------|--------------------------------|------------|------------|----------------|-------|--------------|-------|
| NATURE OF CONVEYANCE: | ASSIGNMENT | | | | | | | | | | |
| CONVEYING PARTY DATA | | | | | | | | | | | |
| <table border="1"> <thead> <tr> <th>Name</th> <th>Execution Date</th> </tr> </thead> <tbody> <tr> <td>Patrice M. Parris</td> <td>04/13/2012</td> </tr> <tr> <td>Weize Chen</td> <td>04/13/2012</td> </tr> </tbody> </table> | | Name | Execution Date | Patrice M. Parris | 04/13/2012 | Weize Chen | 04/13/2012 | | | | |
| Name | Execution Date | | | | | | | | | | |
| Patrice M. Parris | 04/13/2012 | | | | | | | | | | |
| Weize Chen | 04/13/2012 | | | | | | | | | | |
| RECEIVING PARTY DATA | | | | | | | | | | | |
| <table border="1"> <tr> <td>Name:</td> <td>Freescall Semiconductor, Inc.</td> </tr> <tr> <td>Street Address:</td> <td>6501 William Cannon Drive West</td> </tr> <tr> <td>City:</td> <td>Austin</td> </tr> <tr> <td>State/Country:</td> <td>TEXAS</td> </tr> <tr> <td>Postal Code:</td> <td>78735</td> </tr> </table> | | Name: | Freescall Semiconductor, Inc. | Street Address: | 6501 William Cannon Drive West | City: | Austin | State/Country: | TEXAS | Postal Code: | 78735 |
| Name: | Freescall Semiconductor, Inc. | | | | | | | | | | |
| Street Address: | 6501 William Cannon Drive West | | | | | | | | | | |
| City: | Austin | | | | | | | | | | |
| State/Country: | TEXAS | | | | | | | | | | |
| Postal Code: | 78735 | | | | | | | | | | |
| PROPERTY NUMBERS Total: 1 | | | | | | | | | | | |
| <table border="1"> <thead> <tr> <th>Property Type</th> <th>Number</th> </tr> </thead> <tbody> <tr> <td>Application Number:</td> <td>13448062</td> </tr> </tbody> </table> | | Property Type | Number | Application Number: | 13448062 | | | | | | |
| Property Type | Number | | | | | | | | | | |
| Application Number: | 13448062 | | | | | | | | | | |
| CORRESPONDENCE DATA | | | | | | | | | | | |
| <p>Fax Number: (312)291-0864 Phone: 312-291-0860 Email: jpadalino@lsk-iplaw.com <i>Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent via US Mail.</i></p> <p>Correspondent Name: Lempia Summerfield Katz LLC/Freescall Address Line 1: One North LaSalle Street Address Line 2: Suite 2900 Address Line 4: Chicago, ILLINOIS 60602</p> | | | | | | | | | | | |
| ATTORNEY DOCKET NUMBER: | 012668-11004A | | | | | | | | | | |
| NAME OF SUBMITTER: | G. Christopher Braidwood | | | | | | | | | | |
| Total Attachments: 2 source=Assignment#page1.tif source=Assignment#page2.tif | | | | | | | | | | | |

CH \$40.00 13448062

ASSIGNMENT AND AGREEMENT

For good and valuable consideration, the receipt of which is hereby acknowledged, we, Patrice M. Parris and Weize Chen, have sold, assigned and transferred, and do hereby sell, assign and transfer, unto FREESCALE SEMICONDUCTOR, INC., a corporation of the State of Delaware, having its principal office in Austin, State of Texas, United States of America, and its successors, assigns, and legal representatives, the entire right, title and interest for the United States of America in and to certain inventions relating to improvements in a "Semiconductor Device with False Drain" (Docket No. 012668-11004A), described, illustrated and claimed in an application for Letters Patent of the United States of America executed by us on the dates indicated by our signatures below, together with the entire right, title and interest in and to the application, and in and to Letters Patent which may be issued upon the application, and upon any division, extension, continuation or reissue thereof.

We hereby also sell, assign and transfer unto FREESCALE SEMICONDUCTOR, INC., the entire right, title and interest in and to the invention and in and to applications for Letters Patent therefor in all countries foreign to the United States of America, including all rights under any and all international conventions and treaties in respect of the invention and the applications for Letters Patent in foreign countries, and we further authorize FREESCALE SEMICONDUCTOR, INC. to apply for Letters Patent in foreign countries directly in its own name, and to claim priority of the filing date of the application for Letters Patent of the United States of America under the provisions of any and all international conventions and treaties.

We hereby authorize and request the Commissioner of Patents of the United States of America to issue Letters Patent upon the aforesaid application, division, extension, continuation or reissue, to FREESCALE SEMICONDUCTOR, INC., for the sole use and benefit of FREESCALE SEMICONDUCTOR, INC., its successors, assigns and legal representatives, to the full end of the term for which Letters Patent may be granted, the same as they would have been held and enjoyed by me had this assignment not been made, and we hereby authorize and request the equivalent authorities in foreign countries to issue the patents of their respective countries to FREESCALE SEMICONDUCTOR, INC.

We agree that, when requested, we will, without charge to FREESCALE SEMICONDUCTOR, INC., but at its expense, sign all papers, take all rightful oaths, and

do all acts which may be necessary, desirable or convenient for securing and maintaining patents for the inventions in any and all countries and for vesting title thereto in FREESCALE SEMICONDUCTOR, INC., its successors, assigns and legal representatives or nominees.

We covenant with FREESCALE SEMICONDUCTOR, INC., its successors, assigns and legal representatives, that the interest and property hereby conveyed is free from all prior assignment, grant, mortgage, license or other encumbrance.

Patrice M. Parris Date: 4/13/2012
Patrice M. Parris

Witness: Marie E. Borucki 4/13/2012 MARIE E. BORUCKI

Witness: MD. M. Hoque 4/13/2012 MD M HOQUE

Weize Chen Date: 4/13/2012
Weize Chen

Witness: Marie E. Borucki 4/13/2012 MARIE E. BORUCKI

Witness: MD. M. Hoque 4/13/2012 MD M HOQUE